AT2324E

110V N-Channel MOSFET

Features

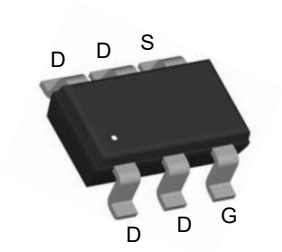
- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

Product Summary

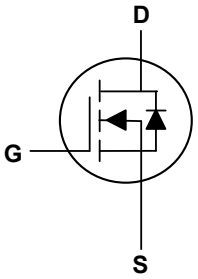
V_{DS}	110	V
I_D	3	A
$R_{DS(ON)}$ (at V_{GS}=10V)	280	mΩ

Applications

- High Frequency Point-of-Load,Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



TSOP6 Top View



Absolute Maximum Ratings(T_A=25℃, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	110	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current[1]	I_D@T_A=25℃	3	A
Continuous Drain Current[1]	I_D@T_A=70℃	2	A
Pulsed Drain Current[2]	I_{DM}	10	A
Total Power Dissipation[3]	P_D@T_A=25℃	1.25	W
Total Power Dissipation[3]	P_D@T_A=70℃	0.8	W
Storage Temperature Range	T_{STG}	-55 to 150	℃
Operating Junction Temperature Range	T_J	-55 to 150	℃

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient[1](t ≤10s)	$R_{\theta JA}$	---	62.5	℃/W
Thermal Resistance Junction-Ambient[1](Steady State)		---	110	℃/W

Electrical Characteristics (T_J=25℃, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V , I_D=250uA	110	---	---	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V , I_D=3A	---	260	280	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS} , I_D =250uA	1	2	2.5	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=80V, V_{GS}=0V , T_A=25℃	---	---	1	uA
		V_{DS}=80V, V_{GS}=0V, T_A=125℃	---	---	5	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
On state drain current	$I_{D(ON)}$	V_{GS}=10V , V_{DS}=5V	3	---	---	A
Forward Transconductance	gfs	V_{DS}=10V , I_D=3A	---	2.4	---	S
Total Gate Charge	Q_g	V_{DS}=50V , V_{GS}=4.5V , I_D=1.5A	---	4.1	---	nC
Gate-Source Charge	Q_{gs}		---	1.4	---	
Gate-Drain Charge	Q_{gd}		---	1.9	---	
Turn-On Delay Time	$T_{d(on)}$	V_{DD}=25V , V_{GS}=10V , R_G=6Ω, I_D=1.5A, R_L=33.3Ω	---	5.7	---	ns
Rise Time	T_r		---	4.3	---	
Turn-Off Delay Time	$T_{d(off)}$		---	12.8	---	
Fall Time	T_f		---	4.4	---	
Input Capacitance	C_{iss}	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	332	---	pF
Output Capacitance	C_{oss}		---	40	---	
Reverse Transfer Capacitance	C_{rss}		---	29	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current[1]	I_S	T_A=25℃	---	---	2.5	A
Diode Forward Voltage[2]	V_{SD}	V_{GS}=0V, I_S=1A , T_J=25℃	---	---	1.2	V

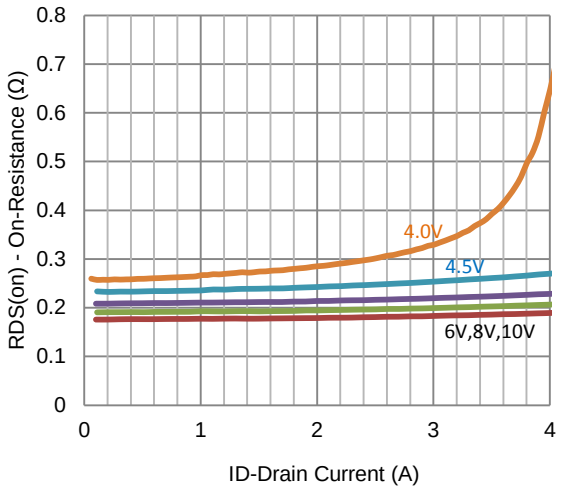
Note:

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

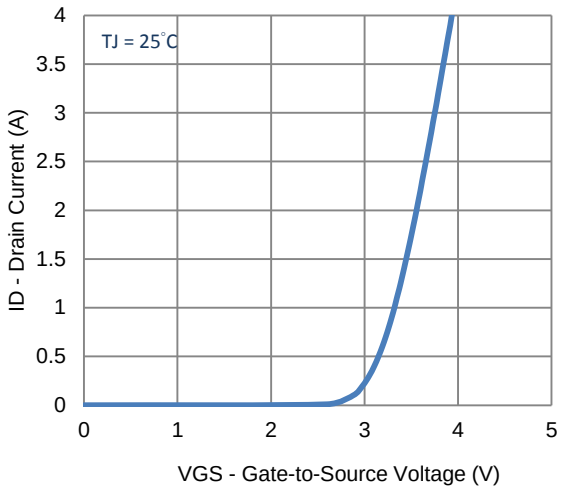
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The power dissipation is limited by 150℃ junction temperature

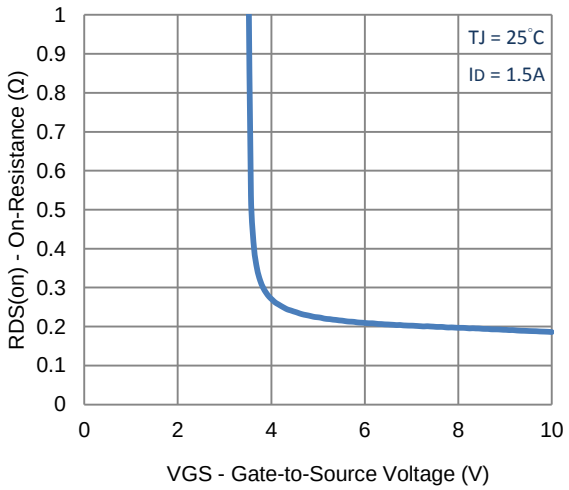
Typical Characteristics



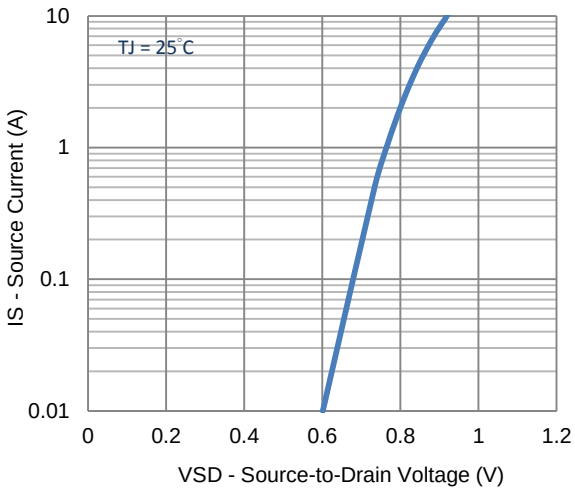
1. On-Resistance vs. Drain Current



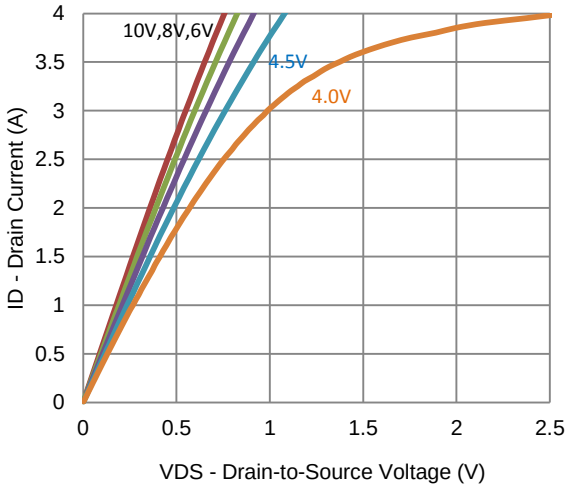
2. Transfer Characteristics



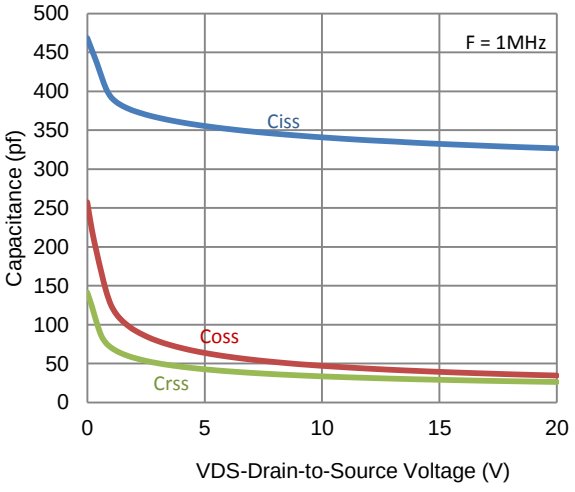
3. On-Resistance vs. Gate-to-Source Voltage



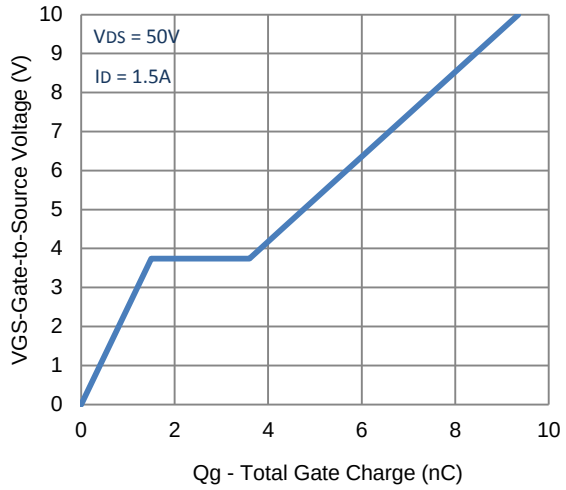
4. Drain-to-Source Forward Voltage



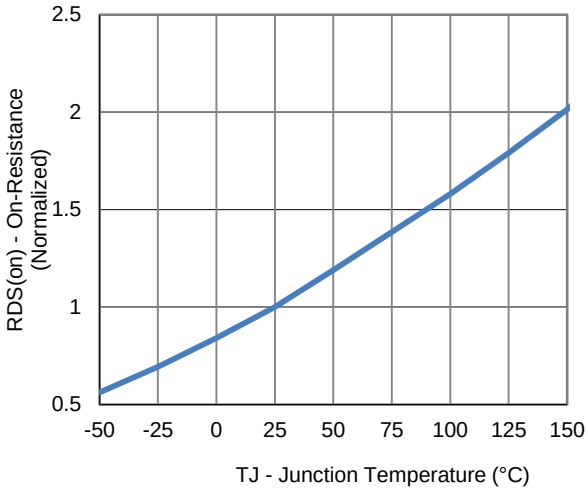
5. Output Characteristics



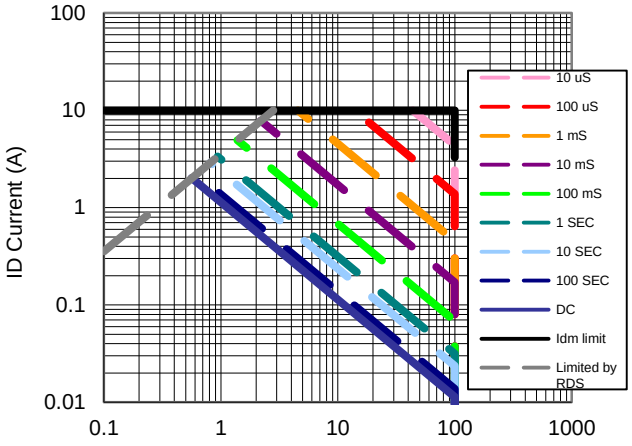
6. Capacitance



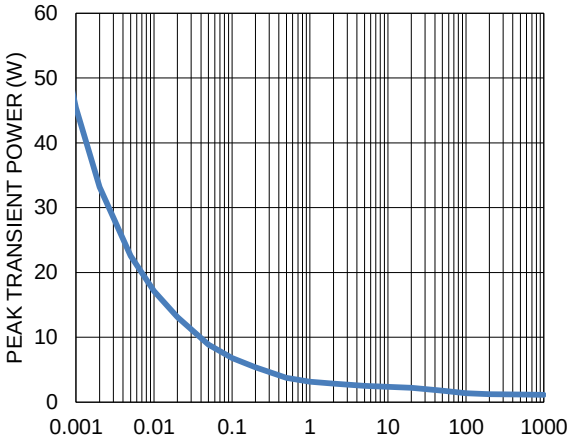
7. Gate Charge



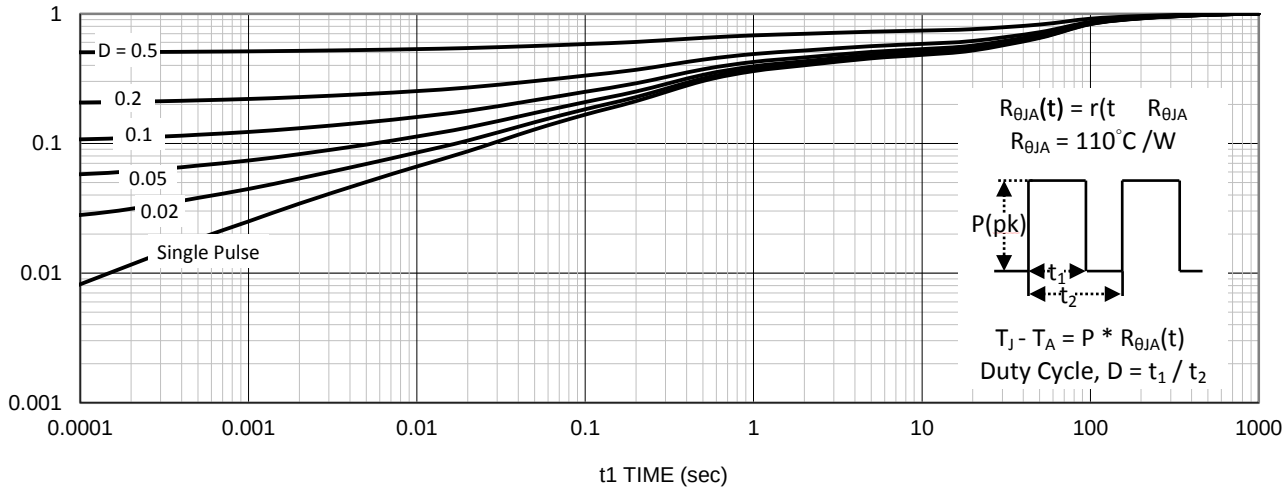
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

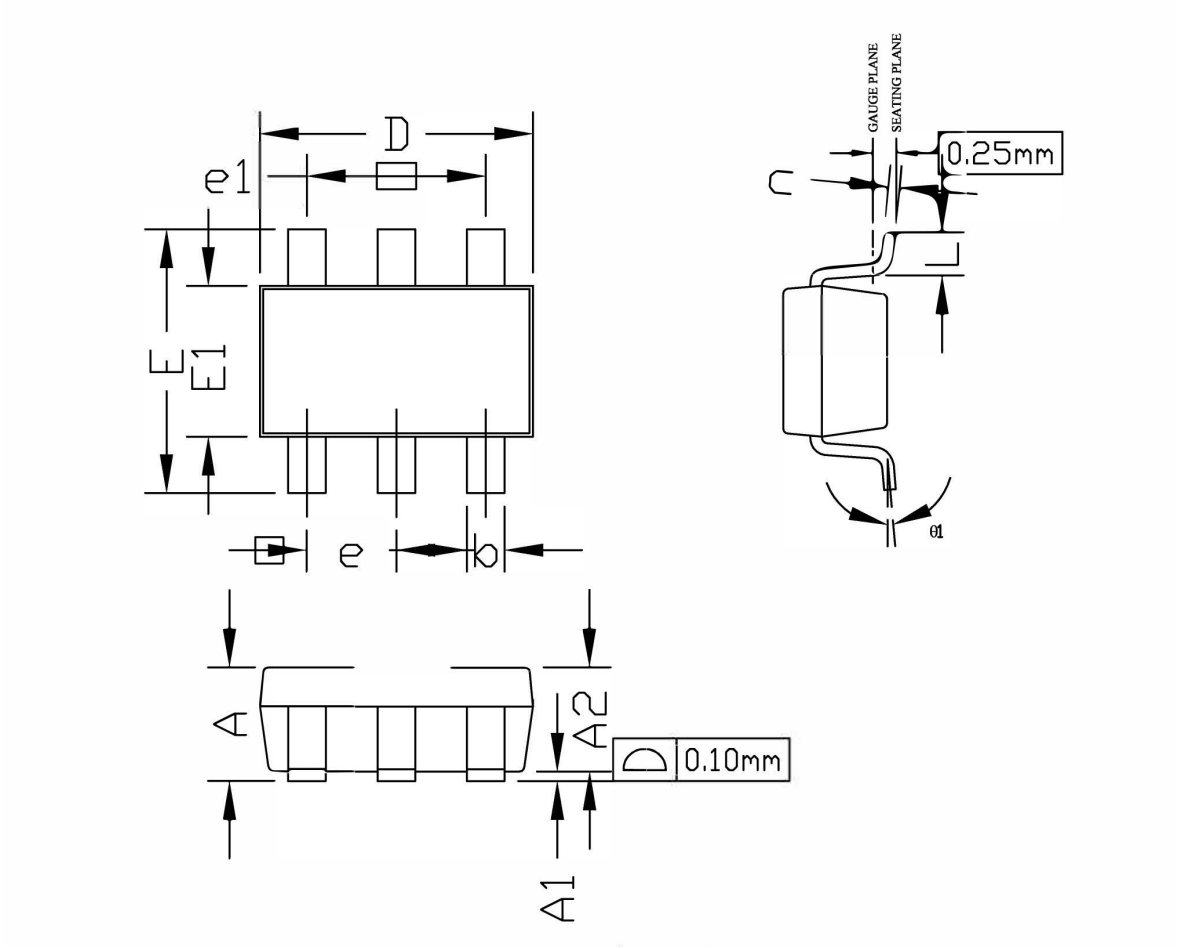


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

TSOP6 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.80	1.00	1.25	**E**	2.50	2.80	3.10
A1	0.00	---	0.15	**E1**	1.50	1.60	1.70
A2	0.80	1.10	1.20	**e**	0.95 REF		
b	0.25	0.35	0.45	**e1**	1.90 REF		
c	0.08	0.13	0.20	**L**	0.30	0.45	0.60
D	2.70	2.90	3.10	**θ1**	0°		8°